



March 2006

# FDD8796/FDU8796

## N-Channel PowerTrench<sup>®</sup> MOSFET

25V, 35A, 5.7mΩ



### General Description

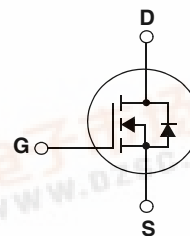
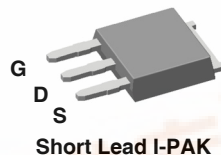
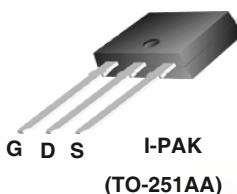
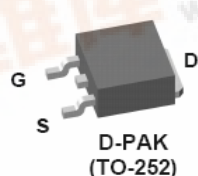
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$  and fast switching speed.

### Application

- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture

### Features

- Max  $r_{DS(on)}$  = 5.7mΩ at  $V_{GS}$  = 10V,  $I_D$  = 35A
- Max  $r_{DS(on)}$  = 8.0mΩ at  $V_{GS}$  = 4.5V,  $I_D$  = 35A
- Low gate charge:  $Q_{g(10)}$  = 37nC(Typ),  $V_{GS}$  = 10V
- Low gate resistance
- Avalanche rated and 100% tested
- RoHS Compliant



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	25	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current -Continuous (Package Limited)	35	A
	-Continuous (Die Limited)	98	
	-Pulsed (Note 1)	305	
$E_{AS}$	Single Pulse Avalanche Energy (Note 2)	91	mJ
$P_D$	Power Dissipation	88	W
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to 175	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case TO_252, TO_251	1.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO_252, TO_251	100	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient TO-252, 1in <sup>2</sup> copper pad area	52	°C/W

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8796	FDD8796	TO-252AA	13"	12mm	2500 units
FDU8796	FDU8796	TO-251AA	N/A (Tube)	N/A	75 units
FDD8796	FDU8796_F071	TO-251AA	N/A (Tube)	N/A	75 units

FDD8796/FDU8796 N-Channel PowerTrench<sup>®</sup> MOSFET

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$B_{VDSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	25			V
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		7		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{V}$ $V_{GS} = 0\text{V}$ $T_J = 150^\circ\text{C}$			1 250	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	1.2	1.8	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-6.7		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 35\text{A}$		4.5	5.7	m $\Omega$
		$V_{GS} = 4.5\text{V}$ , $I_D = 35\text{A}$		6.0	8.0	
		$V_{DS} = 10\text{V}$ , $I_D = 35\text{A}$ $T_J = 175^\circ\text{C}$		6.9	9.5	

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 13\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$		1960	2610	pF
$C_{oss}$	Output Capacitance			455	605	pF
$C_{rss}$	Reverse Transfer Capacitance			315	475	pF
$R_G$	Gate Resistance	$f = 1\text{MHz}$		1.1		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 13\text{V}$ , $I_D = 35\text{A}$ $V_{GS} = 10\text{V}$ , $R_{GS} = 20\Omega$		10	20	ns
$t_r$	Rise Time			24	39	ns
$t_{d(off)}$	Turn-Off Delay Time			99	158	ns
$t_f$	Fall Time			57	91	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0$ to $10\text{V}$	$V_{DD} = 13\text{V}$ , $I_D = 35\text{A}$ , $I_g = 1.0\text{mA}$	37	52	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0$ to $5\text{V}$		19	27	nC
$Q_{gs}$	Gate to Source Gate Charge			6		nC
$Q_{gd}$	Gate to Drain Charge			6		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Voltage	$V_{GS} = 0\text{V}$ , $I_S = 35\text{A}$		0.9	1.25	V
		$V_{GS} = 0\text{V}$ , $I_S = 15\text{A}$		0.8	1.0	V
$t_{rr}$	Reverse Recovery Time	$I_F = 35\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$		30	45	ns
$Q_{rr}$	Reverse Recovery Charge	$I_F = 35\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$		23	35	nC

**Notes:**

- 1: Pulse time < 300 $\mu\text{s}$ , Duty cycle = 2%.  
 2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.3\text{mH}$ ,  $I_{AS} = 24.7\text{A}$ ,  $V_{DD} = 23\text{V}$ ,  $V_{GS} = 10\text{V}$ .

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

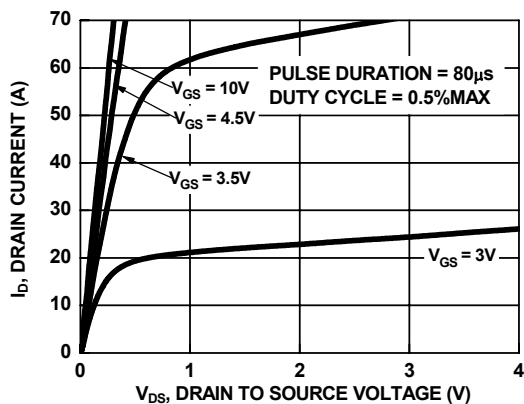


Figure 1. On Region Characteristics

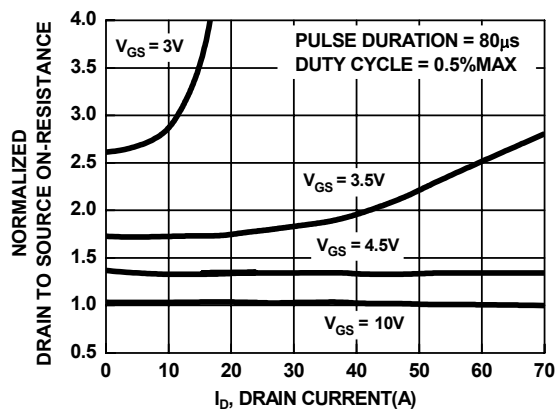


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

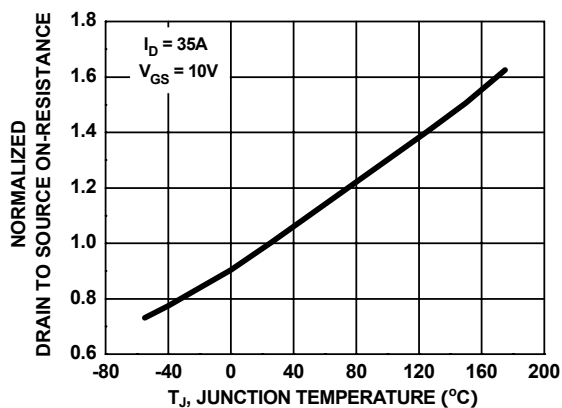


Figure 3. Normalized On Resistance vs Junction Temperature

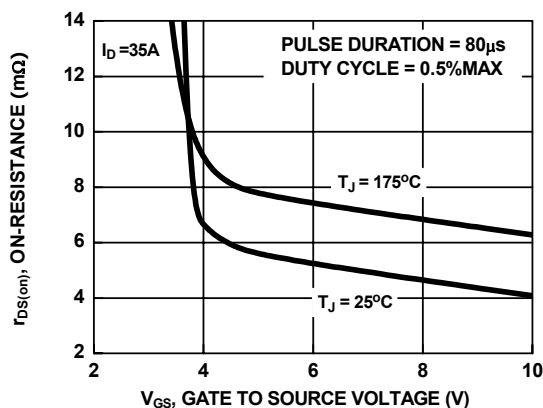


Figure 4. On-Resistance vs Gate to Source Voltage

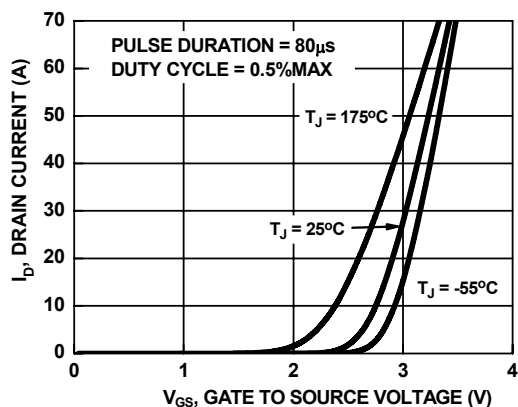


Figure 5. Transfer Characteristics

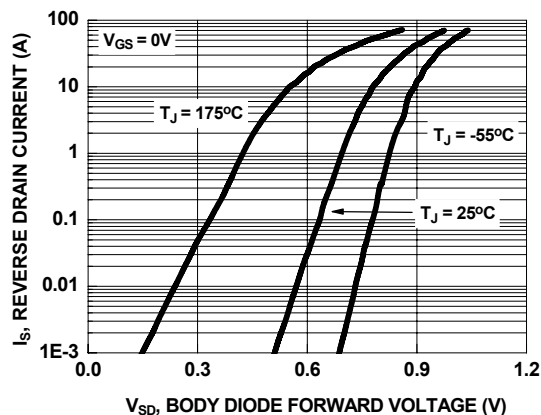


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

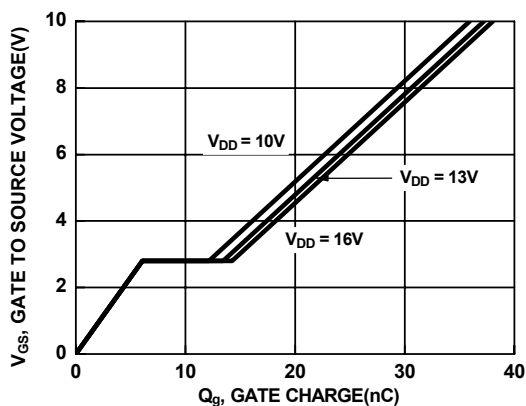


Figure 7. Gate Charge Characteristics

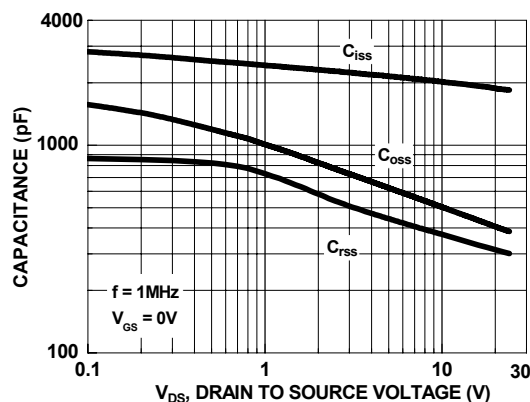


Figure 8. Capacitance vs Drain to Source Voltage

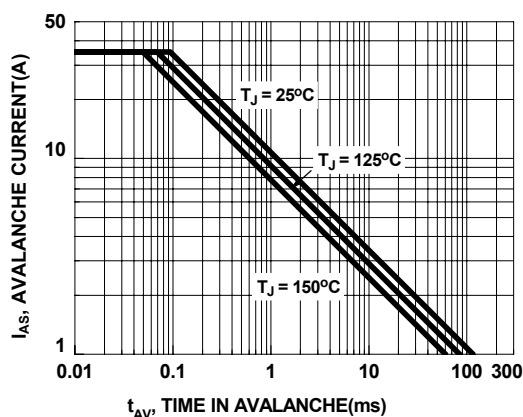


Figure 9. Unclamped Inductive Switching Capability

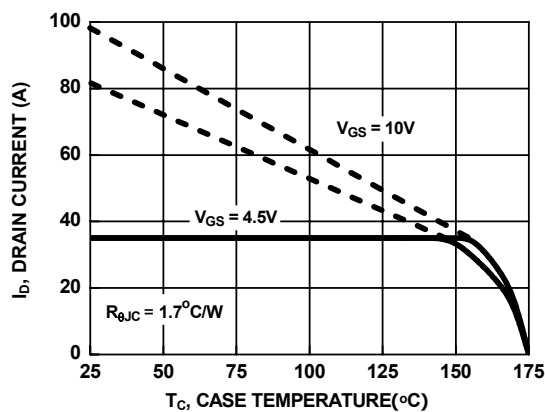


Figure 10. Maximum Continuous Drain Current vs Case Temperature

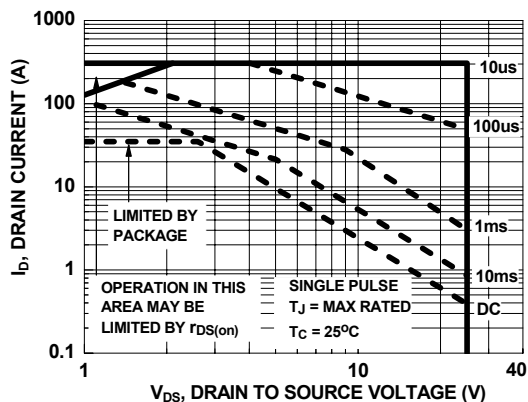


Figure 11. Forward Bias Safe Operating Area

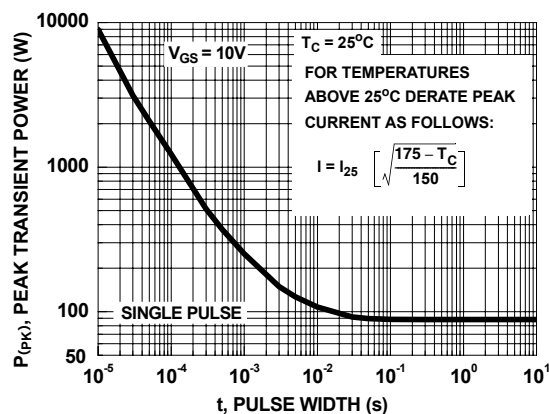
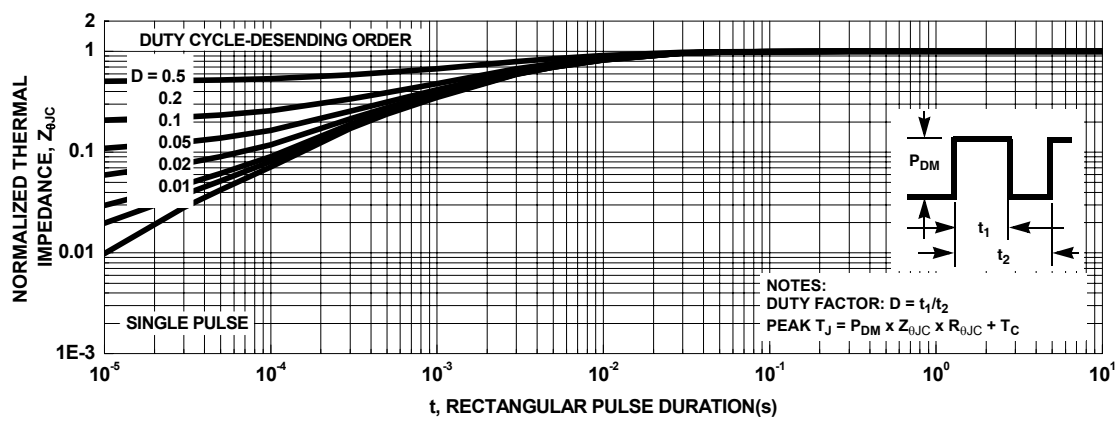


Figure 12. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



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